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APPLICATION NO.	FII	LING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/813,085	0	3/31/2004	Toshihide Kikkawa	040153 5120	
23850	7590	10/18/2005		EXAM	INER
ARMSTRONG, KRATZ, QUINTOS, HANSON & BROOKS, LLP				VU, HUNG K	
1725 K STR	EET, NW				
SUITE 1000)			ART UNIT	PAPER NUMBER
WASHING	TON, DC	20006		2811	

DATE MAILED: 10/18/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)		
	10/813,085	KIKKAWA, TOSHIHIDE		
Office Action Summary	Examiner	Art Unit		
	Hung Vu	2811		
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with the c	orrespondence address		
A SHORTENED STATUTORY PERIOD FOR REPL WHICHEVER IS LONGER, FROM THE MAILING D. Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. If NO period for reply is specified above, the maximum statutory period Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION (36(a)). In no event, however, may a reply be tin will apply and will expire SIX (6) MONTHS from the cause the application to become ABANDONE	N. nely filed the mailing date of this communication. D (35 U.S.C. § 133).		
Status				
 1) ⊠ Responsive to communication(s) filed on 26 Journal 2a) ☐ This action is FINAL. 2b) ☑ This 3) ☐ Since this application is in condition for allowange closed in accordance with the practice under Exercise 1. 	s action is non-final. nce except for formal matters, pro			
Disposition of Claims				
4) ⊠ Claim(s) 1-15 is/are pending in the application 4a) Of the above claim(s) 13-15 is/are withdray 5) ⊠ Claim(s) 1-3 and 9-12 is/are allowed. 6) ⊠ Claim(s) 4-8 is/are rejected. 7) □ Claim(s) is/are objected to. 8) □ Claim(s) are subject to restriction and/or	wn from consideration.			
Application Papers				
9) The specification is objected to by the Examine 10) The drawing(s) filed on is/are: a) accomplicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the Examine 11.	cepted or b) objected to by the drawing(s) be held in abeyance. Se ction is required if the drawing(s) is ob	e 37 CFR 1.85(a). ejected to. See 37 CFR 1.121(d).		
Priority under 35 U.S.C. § 119				
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 				
Attachment(s) 1) \(\subseteq \) Notice of References Cited (PTO-892) 2) \(\subseteq \) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) \(\subseteq \) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08 Paper No(s)/Mail Date \(\frac{3/31/04}{2} \).	4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal I 6) Other:			

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DETAILED ACTION

Election/Restrictions

1. Applicant's election without traverse of Invention of Group I, Claims 1-12 in the reply filed on 07/26/05 is acknowledged.

Claims 13-15 are withdrawn from further consideration pursuant to 37 CFR 1.142(b) as being drawn to a nonelected Invention, there being no allowable generic or linking claim.

Election was made without traverse in the reply filed on 07/26/05.

Specification

2. The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed.

Claim Rejections - 35 USC § 112

3. The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claim 8 is rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

In claim 8, lines 3-5, the phrase at least one portion having the compositional ratio x which exceeds the above-described range" is unclear as to whether the independent claim 4 does not recited any range of the compositional ratio x.

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Claim Rejections - 35 USC § 102

4. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 4 and 8 are rejected under 35 U.S.C. 102(e) as being anticipated by Yoshida et al. (PN 6,897,495).

Yoshida et al. discloses, as shown in Figure 1, a compound semiconductor device having a stack formed on a substrate,

the stack comprising a first nitride semiconductor layer (14) which later becomes an electron transit layer;

a second nitride semiconductor layer (16) which later forms an electron supply layer and contains Al;

a third nitride semiconductor layer (24b) having an Al content of zero or smaller than that of the second nitride semiconductor layer;

the second nitride semiconductor layer is formed in a thickness so as to satisfy the following relation:

$$-80x + 29 < d < -180x + 52$$

where x denotes the compositional ratio of Al and d (nm) denotes the thickness. Note that since no value of the compositional ratio of Al of any layer is provided, the examiner assume x is equal to zero.

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Regarding claim 8, Yoshida et al. discloses the second nitride semiconductor layer include

therein at least one portion having the compositional ratio x which not larger than 0.3.

Claim Rejections - 35 USC § 103

5. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all

obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person

such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the

manner in which the invention was made.

Claims 5-7 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yoshida et al.

(PN 6,897,495).

Although Yoshida et al. does not teach the thickness of the third nitride semiconductor layer, the

compositional ratio x of Al and/or the thickness d of the second nitride semiconductor layer, and

a sheet resistance of the stack, as that claimed by Applicants, however, it would have been

obvious to one having ordinary skill in the art at the time the invention was made to form the

third nitride semiconductor layer having a desired thickness, the second nitride semiconductor

layer having a desired compositional ratio and/or thickness, and the stack having a desired sheet

resistance, since it has been held that discovering an optimum value of a result effective variable

involves only routine skill in the art. In re Boesch, 617 F.2d 272, 205 USPQ 215 (CCPA 1980).

Allowable Subject Matter

6. Claims 1-3 and 9-12 are allowed.

7. The following is an examiner's statement of reasons for allowance:

Applicant's claims 1-3 and 9-12 are allowable over the references of record because none of these references disclose or can be combined to yield the claimed compound semiconductor device having a stack comprising a third nitride semiconductor layer having a nitrogen vacancy ratio of 20% or less within a range as deep as 2 nm or less from the surface thereof, in combination with the remaining claimed limitations of claim 1.

Conclusion

8. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Hung Vu whose telephone number is (571) 272-1666. The examiner can normally be reached on Mon-Thurs 6:00-3:30, alternate Fri 7:00-3:30.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Steven Loke can be reached on (571) 272 - 1657. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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Vu

October 13, 2005

Hung Vu

Primary Examiner